

SF115A

Product specifications

Type	Transistor Silicon NPN
Case	X13
Vbr CBO	50
Vbr CEO	30
Max. PD (W)	150m
Derate (Amb) (W/°C)	1.2m
hfe	50
Ic Max. (A)	30m
Icbo Max. @ Vcb Max. (A)	50n
Polarity	NPN
Trans. Freq (Hz) Min.	200M
@ VCE (test) (V)	10
Oper. Temp (°C) Max.	150
@ Ic (A)	1.0m
Pinout Equivalence Number	3-10
Pkg Style	TO-92var
Surface Mounted Yes/No	NO
Maximum Collector Power Dissipation (Pc)	0.15 W
Maximum Collector-Base Voltage Vcb	50 V
Maximum Collector-Emitter Voltage Vce	30 V
Maximum Emitter-Base Voltage Veb	5 V
Maximum Collector Current Ic max	0.03 A
Max. Operating Junction Temperature (Tj)	125 °C
Collector Capacitance (Cc)	3 pF
Transition Frequency (ft):	200 MHz
Forward Current Transfer Ratio (hFE), MIN	50